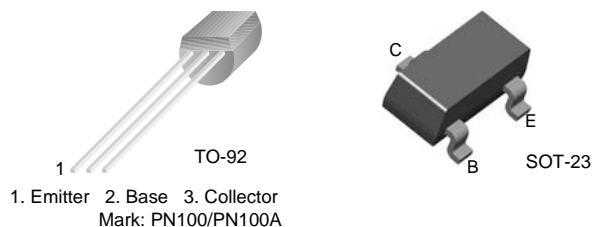


PN100/PN100A/MMBT100/MMBT100A

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300mA.
- Sourced from process 10.



Absolute Maximum Ratings* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CEO}	Collector-Emitter Voltage		45
V_{CBO}	Collector-Base Voltage		75
V_{EBO}	Emitter-Base Voltage		6.0
I_C	Collector current	- Continuous	500
T_J, T_{stg}	Junction and Storage Temperature		-55 ~ +150

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1. These ratings are based on a maximum junction temperature of 150 degrees C.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

* Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%

Thermal Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.		Units
		PN100 PN100A	*MMBT100 *MMBT100A	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	$^\circ\text{C}/\text{W}$

* Device mounted on FR-4 PCB 1.6" \times 1.6" \times 0.06."

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	75		V
BV_{CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 1\text{mA}, I_B = 0$	45		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector-Base Cutoff Current	$V_{CB} = 60\text{V}$		50	nA
I_{CES}	Collector-Emiitter Cutoff Current	$V_{CE} = 40\text{V}$		50	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4\text{V}$		50	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}^*$ $I_C = 150\text{mA}, V_{CE} = 5.0\text{V}^*$	100 100A 100 100A 100 100A	80 240 100 300 100 100	 450 600 350
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 200\text{mA}, I_B = 20\text{mA}$		0.2 0.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 200\text{mA}, I_B = 20\text{mA}$		0.85 1.0	V V
Small Signal Characteristics					
f_T	Current Gain Bandwidth Product	$V_{CE} = 20\text{V}, I_C = 20\text{mA}$		250	MHz
C_{obo}	Output Capacitance	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}$			4.5 pF
NF	Noise Figure	$I_C = 100\mu\text{A}, V_{CE} = 5.0\text{V}$ $R_G = 2.0\text{k}\Omega, f = 1.0\text{KHz}$	100 100A		5.0 4.0 dB

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

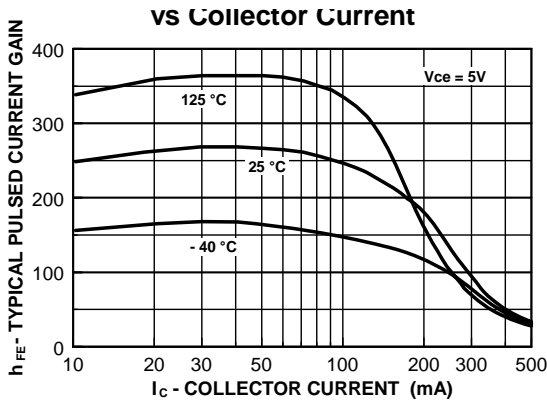


Figure 1. Typical Pulsed Current Gain vs Collector Current

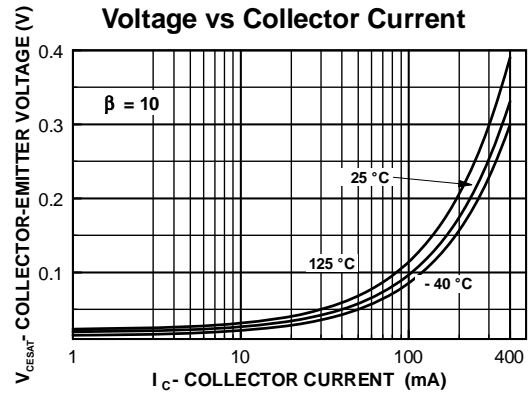


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

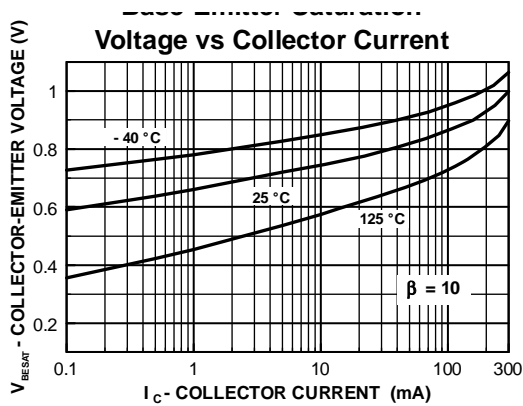


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

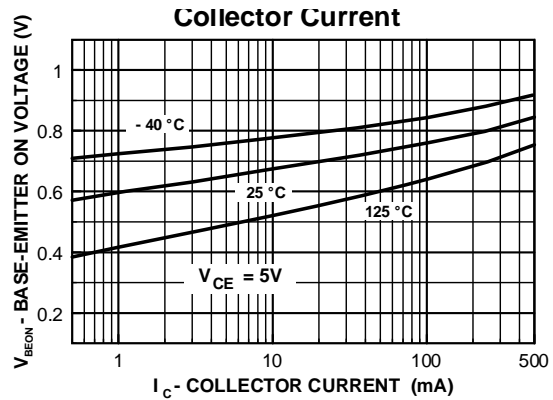


Figure 4. Base-Emitter On Voltage vs Collector Current

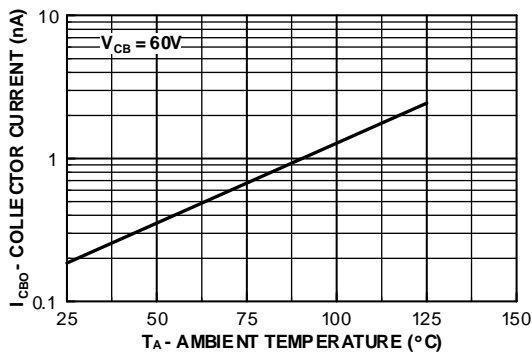


Figure 5. Collector Cutoff Current vs Ambient Temperature

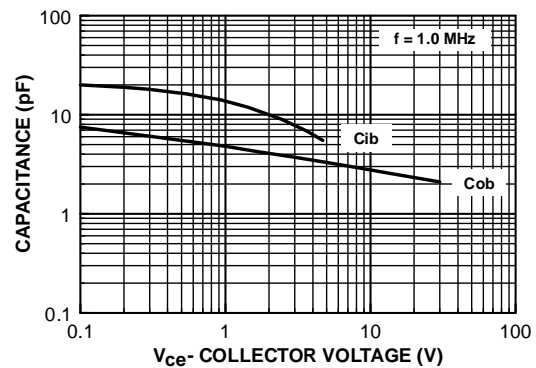


Figure 6. Input and Output Capacitance vs Reverse Voltag

Typical Characteristics (Continued)

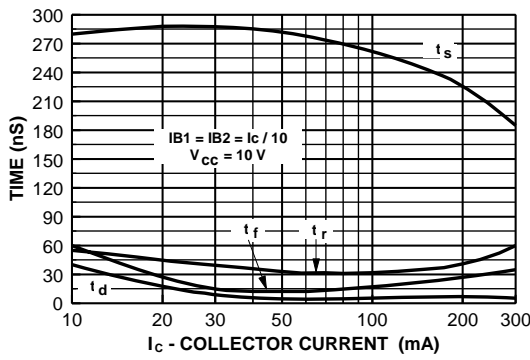


Figure 7. Switching Times vs Collector Current

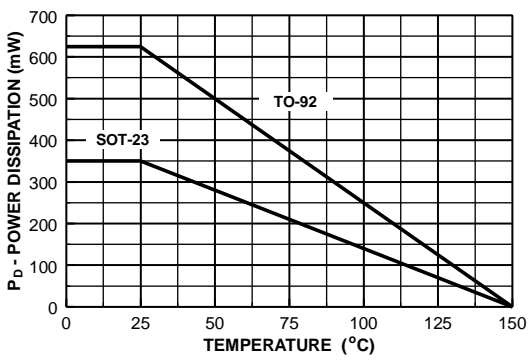
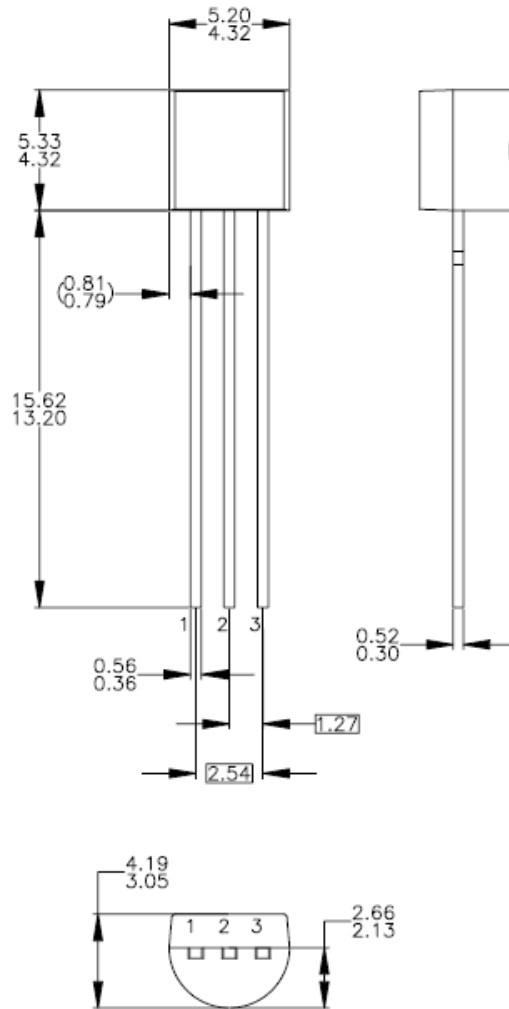


Figure 8. Power Dissipation vs Ambient Temperature

Package Dimension (TO92)



NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DRAWING CONFORMS TO ASME Y14.5M-1994.
- TO-92 (92,94,96,97,98) PIN CONFIGURATION:

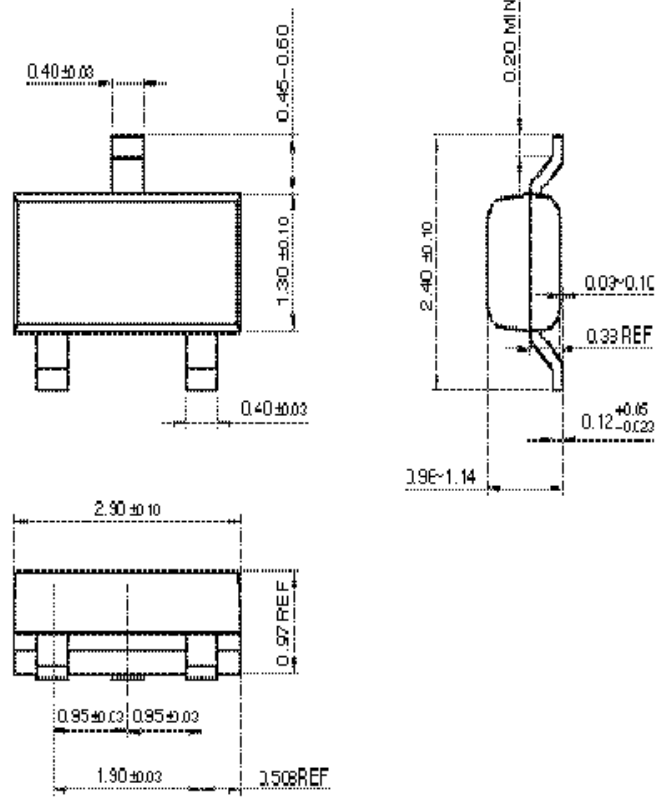
	92	94	96	97	98
PIN	P F M	P F M	B F M	P F M	P F M
1	E S S	E S S	B D G	C G D	C G D
2	B D G	C G D	E S S	B D G	E S S
3	C G D	B D G	C G D	E S S	B D G

LEGEND:

P - BIPOLAR E - EMITTER D - DRAIN
F - JFET B - BASE S - SOURCE
M - DMOS C - COLLECTOR G - GATE

- FOR PACKAGE 92, 94, 96, 97 AND 98:
PIN CONFIGURATION DRAIN "D" AND SOURCE "S"
ARE INTERCHANGEABLE AT JFET "F" OPTION.
- DRAWING FILENAME: MKT-2A030REV3.

Package Dimension (SOT23)





TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx [®]	Green FPST [™]	Power247 [®]	SuperSOT [™] -8
Build it Now [™]	Green FPST [™] e-Series [™]	POWEREDGE [®]	SyncFET [™]
CorePLUS [™]	GTO [™]	Power-SPM [™]	The Power Franchise [®]
CROSSVOLT [™]	i-Lo [™]	PowerTrench [®]	the power franchise
CTL [™]	IntelliMAX [™]	Programmable Active Droop [™]	QFET [®]
Current Transfer Logic [™]	ISOPANAR [™]	QFET [®]	TinyBoost [™]
EcoSPARK [®]	MegaBuck [™]	QST [™]	TinyBuck [™]
F [®]	MICROCOUPLER [™]	QT Optoelectronics [™]	TinyLogic [®]
Fairchild [®]	MicroFET [™]	Quiet Series [™]	TINYOPTO [™]
Fairchild Semiconductor [®]	MicroPak [™]	RapidConfigure [™]	TinyPower [™]
FACT Quiet Series [™]	MillerDrive [™]	SMART START [™]	TinyPWM [™]
FACT [®]	Motion-SPM [™]	SPM [®]	TinyWire [™]
FAST [®]	OPTOLOGIC [®]	STEALTH [™]	μSerDes [™]
FastvCore [™]	OPTOPLANAR [®]	SuperFET [™]	UHC [®]
FPST [™]	®	SuperSOT [™] -3	UniFET [™]
FRFET [®]	PDP-SPM [™]	SuperSOT [™] -6	VCX [™]
Global Power Resource SM	Power220 [®]		

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. I31

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative